

8-Bit Shift Register with **Output Storage Register** (3-State) **MC74VHC595**

The MC74VHC595 is an advanced high speed 8-bit shift register with an output storage register fabricated with silicon gate CMOS technology.

It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHC595 contains an 8-bit static shift register which feeds an 8-bit storage register.

Shift operation is accomplished on the positive going transition of the Shift Clock input (SCK). The output register is loaded with the contents of the shift register on the positive going transition of the Register Clock input (RCK). Since the RCK and SCK signals are independent, parallel outputs can be held stable during the shift operation. And, since the parallel outputs are 3-state, the VHC595 can be directly connected to an 8-bit bus. This register can be used in serial-to-parallel conversion, data receivers, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 5.5 V, allowing the interface of 5 V systems to 3 V systems.

Features

- High Speed: $f_{max} = 185 \text{ MHz}$ (Typ) at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25^{\circ}C$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 1.0 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- -Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and **PPAP** Capable
- These Devices are Pb-Free and are RoHS Compliant





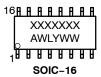


TSSOP-16 **DT SUFFIX** CASE 948F



MN SUFFIX CASE 485AW

MARKING DIAGRAMS







XXXXXXX = Specific Device Code

= Assembly Location

WL.I = Wafer Lot = Year WW, W = Work Week G or ■ = Pb-Free Package

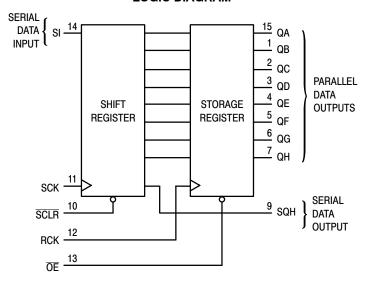
(Note: Microdot may be in either location)

ORDERING INFORMATION

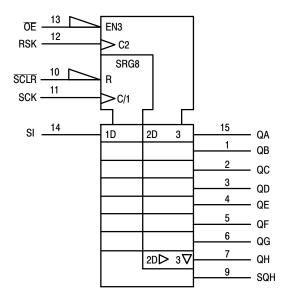
See detailed ordering, marking and shipping information in the package dimensions section on page 10 of this data sheet.

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LOGIC DIAGRAM



IEC LOGIC SYMBOL



FUNCTION TABLE

			Inputs				Resulting F	unction	
Operation	Reset (SCLR)	Serial Input (SI)	Shift Clock (SCK)	Reg Clock (RCK)	Output Enable (OE)	Shift Register Contents	Storage Register Contents	Serial Output (SQH)	Parallel Outputs (QA – QH)
Clear shift register	L	Х	Х	L, H, ↓	L	L	U	L	U
Shift data into shift register	Н	D	1	L, H, ↓	L	$D \rightarrow SR_A;$ $SR_N \rightarrow SR_{N+1}$	U	SR _G →SR _H	U
Registers remains unchanged	Н	Х	L, H, ↓	Х	L	U	**	U	**
Transfer shift register contents to storage register	Н	Х	L, H, ↓	1	L	U	SR _N →STR _N	*	SR _N
Storage register remains unchanged	Х	Х	Х	L, H, ↓	L	*	U	*	U
Enable parallel outputs	Х	Х	Х	Х	L	*	**	*	Enabled
Force outputs into high impedance state	Х	Х	Х	Х	Н	*	**	*	Z

SR = shift register contents STR = storage register contents U = remains unchanged

D = data (L, H) logic level

 \downarrow = High-to-Low

* = depends on Reset and Shift Clock inputs ** = depends on Register Clock input

↑ = Low-to-High

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V
V _{IN}	DC Input Voltage		-0.5 to +6.5	V
V _{OUT}	DC Output Voltage		-0.5 to V _{CC} +0.5	V
I _{IN}	DC Input Current, per Pin		±20	mA
I _{OUT}	DC Output Current, per Pin		±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins		±50	mA
I _{IK}	Input Clamp Current		-20	mA
I _{OK}	Output Clamp Current		±20	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	SOIC-16 QFN16 TSSOP-16	126 118 159	°C/W
P _D	Power Dissipation in Still Air at 25°C	SOIC-16 QFN16 TSSOP-16	995 1062 787	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in.	-
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 N/A	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Applicable to devices with outputs that may be tri-stated.
- 2. Measured with minimum pad spacing on an FR4 board, using 76mm-by-114mm, 2-ounce copper trace no air flow per JESD51-7.
- 3. HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V _{CC}	DC Supply Voltage		2.0	5.5	V
V _{IN}	DC Input Voltage (Note 4)		0	5.5	V
V _{OUT}	DC Output Voltage (Note 4)		0	V _{CC}	V
T _A	Operating Temperature		- 55	+125	°C
t _r , t _f	Input Rise or Fall Rate $ V_{CC} = 3.0 \text{ V to } $		0 0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}		T _A = 25°C	;	T _A = ≤	≤ 85°C	T _A = ≤	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V _{OH}	Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
	VIN = VIH OF VIL	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OH} = -4 \text{ mA} \\ &I_{OH} = -8 \text{ mA} \end{aligned}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
	$V_{IN} = V_{IH}$ or V_{IL}	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OL} = 4 \text{ mA} \\ &I_{OL} = 8 \text{ mA} \end{aligned}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		± 1.0	μΑ
Icc	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			4.0		40.0		40.0	μΑ
I _{OZ}	Three-State Output Off-State Current	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or }$ GND	5.5			± 0.25		± 2.5		± 2.5	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{4.} Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

AC ELECTRICAL CHARACTERISTICS

					T _A = 25°C	;	T _A = ≤	≤ 85°C	T _A = ≤	125°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
f _{max}	Maximum Clock Frequency (50%	$V_{CC} = 3.3 \pm 0.3 \text{ V}$		80	150		70		70		MHz
	Duty Cycle)	$V_{CC} = 5.0 \pm 0.5 \text{ V}$		135	185		115		115		
t _{PLH} , t _{PHL}	Propagation Delay, SCK to	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15pF C _L = 50pF		8.8 11.3	13.0 16.5	1.0 1.0	15.0 18.5	1.0 1.0	15.0 18.5	ns
	SQH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		6.2 7.7	8.2 10.2	1.0 1.0	9.4 11.4	1.0 1.0	9.4 11.4	
t _{PHL}	Propagation Delay,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		8.4 10.9	12.8 16.3	1.0 1.0	13.7 17.2	1.0 1.0	13.7 17.2	ns
	CPLR to SQH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15pF C _L = 50pF		5.9 7.4	8.0 10.0	1.0 1.0	9.1 11.1	1.0 1.0	9.1 11.1	
t _{PLH} , t _{PHL}	Propagation Delay, RCK to	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15pF C _L = 50pF		7.7 10.2	11.9 15.4	1.0 1.0	13.5 17.0	1.0 1.0	13.5 17.0	ns
	QA-QH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15pF C _L = 50pF		5.4 6.9	74 9.4	1.0 1.0	8.5 10.5	1.0 1.0	8.5 10.5	
t _{PZL} , t _{PZH}	Output Enable Time,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		7.5 9.0	11.5 15.0	1.0 1.0	13.5 17.0	1.0 1.0	13.5 17.0	ns
	OE to QA-QH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		4.8 8.3	8.6 10.6	1.0 1.0	10.0 12.0	1.0 1.0	10.0 12.0	
t _{PLZ} ,	Output Disable	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 50pF		12.1	15.7	1.0	16.2	1.0	16.2	ns
t _{PHZ}	Time, OE to QA-QH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 50pF		7.6	10.3	1.0	11.0	1.0	11.0	1
C _{IN}	Input Capacitance				4	10		10		10	pF
C _{OUT}	Three-State Output Capacitance (Output in High-Impedance State), QA-QH				6			10		10	pF

		Typical @ 25°C, V _{CC} = 5.0 V		
C_{PD}	Power Dissipation Capacitance (Note 5)	87	pF	

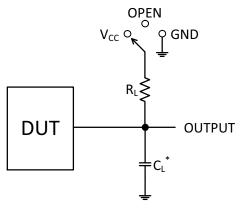
^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS ($C_L = 50 \text{ pF}, V_{CC} = 5.0 \text{ V}$)

		T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.8	1.0	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.8	-1.0	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

TIMING REQUIREMENTS

		V _{CC}	T _A =	: 25°C	T _A = - 40 to 85°C	T _A = - 55 to 125°C	
Symbol	Parameter	V	Тур	Limit	Limit	Limit	Unit
t _{su}	Setup Time, SI to SCK	3.3 5.0		3.5 3.0	3.5 3.0	3.5 3.0	ns
t _{su(H)}	Setup Time, SCK to RCK	3.3 5.0		8.0 5.0	8.5 5.0	8.5 5.0	ns
t _{su(L)}	Setup Time, SCLR to RCK	3.3 5.0		8.0 5.0	9.0 5.0	9.0 5.0	ns
t _h	Hold Time, SI to SCK	3.3 5.0		1.5 2.0	1.5 2.0	1.5 2.0	ns
t _{h(L)}	Hold Time, SCLR to RCK	3.3 5.0		0	0	1.0 1.0	ns
t _{rec}	Recovery Time, SCLR to SCK	3.3 5.0		3.0 2.5	3.0 2.5	3.0 2.5	ns
t _w	Pulse Width, SCK or RCK	3.3 5.0		5.0 5.0	5.0 5.0	5.0 5.0	ns
t _{w(L)}	Pulse Width, SCLR	3.3 5.0		5.0 5.0	5.0 5.0	5.0 5.0	ns

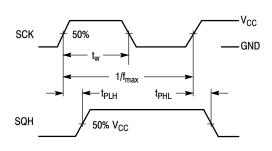


Test	Switch Position	C _L	R_{L}
t _{PLH} / t _{PHL}	Open	See AC Characteristics	1 kΩ
t _{PLZ} / t _{PZL}	V _{CC}	Table	
t _{PHZ} / t _{PZH}	GND		

 $^{\star}C_L$ Includes probe and jig capacitance Input $t_R = t_F = 3 \text{ ns}$

Figure 1. Test Circuit

SWITCHING WAVEFORMS



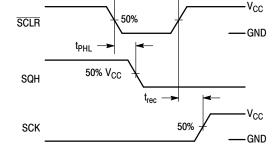


Figure 2.

Figure 3.

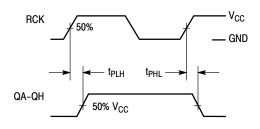
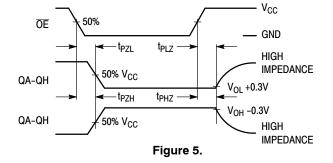
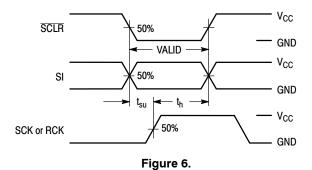


Figure 4.





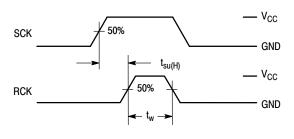


Figure 7.

EXPANDED LOGIC DIAGRAM

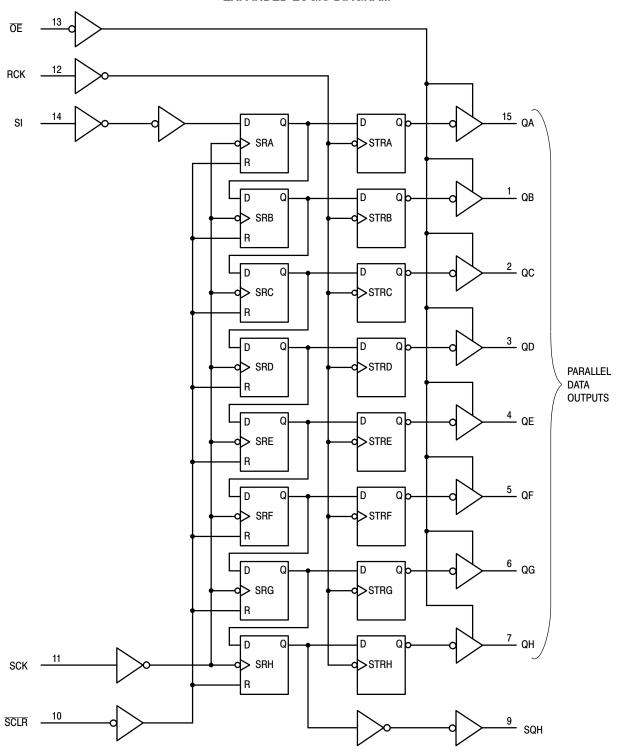
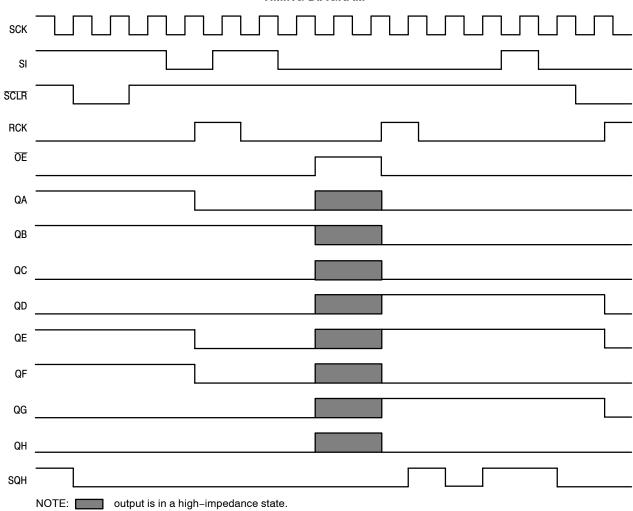
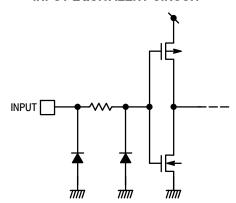


Figure 8.

TIMING DIAGRAM



INPUT EQUIVALENT CIRCUIT



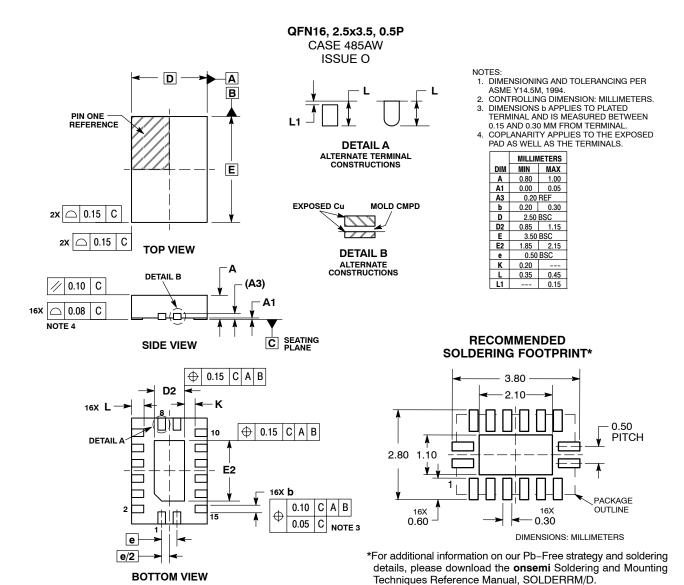
ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MC74VHC595DR2G	VHC595G	SOIC-16	2500 Units / Tape & Reel
MC74VHC595DTR2G	VHC 595	TSSOP-16	2500 Units / Tape & Reel
MC74VHC595DTR2G-Q*	VHC 595	TSSOP-16	2500 Units / Tape & Reel

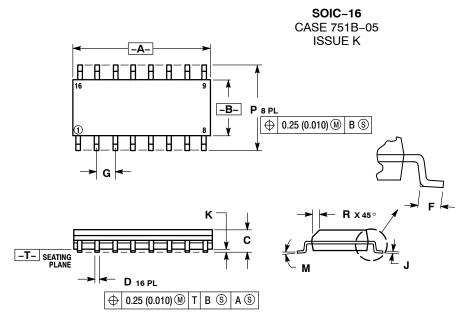
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*-Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS



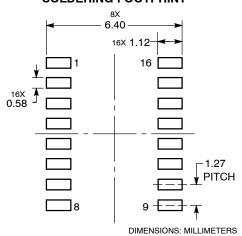
PACKAGE DIMENSIONS



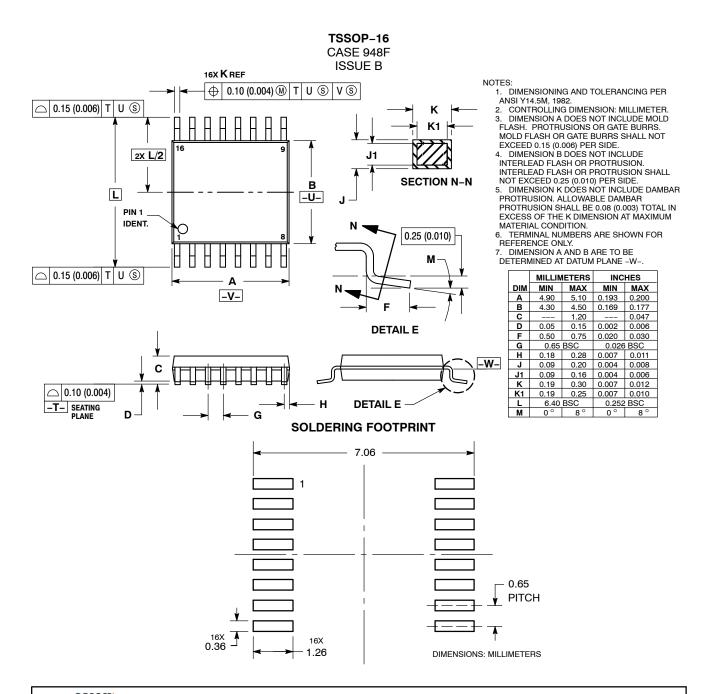
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050	BSC	
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

SOLDERING FOOTPRINT



PACKAGE DIMENSIONS



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